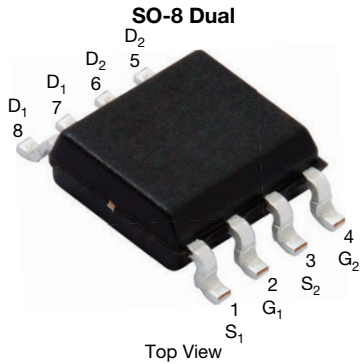


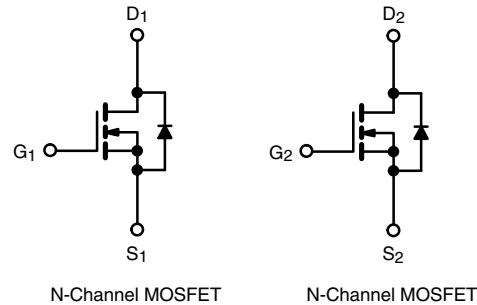
# Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET



## FEATURES

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE GRADE


**RoHS COMPLIANT**  
 HALOGEN FREE


PRODUCT SUMMARY	
V <sub>DS</sub> (V)	60
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 10 V	0.064
R <sub>DS(on)</sub> (Ω) at V <sub>GS</sub> = 4.5 V	0.082
I <sub>D</sub> (A) per leg	5.4
Configuration	Dual

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ9945CEY (for detailed order number please see <a href="http://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current	T <sub>C</sub> = 25 °C	I <sub>D</sub>	5.4	A
	T <sub>C</sub> = 125 °C		3.1	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	3.6	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	21.5	
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	8.5	
Single Pulse Avalanche Energy		E <sub>AS</sub>	3.6	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	4	W
	T <sub>C</sub> = 125 °C		1.3	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	112	°C/W
Junction-to-Foot (Drain)		R <sub>thJF</sub>	38	

### Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		1.5	2	2.5	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	150	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	20	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 3.4\text{ A}$	-	0.045	0.064	$\Omega$
		$V_{GS} = 10\text{ V}$	$I_D = 3.4\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	0.110	
		$V_{GS} = 10\text{ V}$	$I_D = 3.4\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	0.137	
		$V_{GS} = 4.5\text{ V}$	$I_D = 3.7\text{ A}$	-	0.060	0.082	
Forward Transconductance <sup>f</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 3.7\text{ A}$		-	12	-	S
<b>Dynamic <sup>b</sup></b>							
Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	-	383	470	$\mu\text{F}$
Output Capacitance	$C_{OSS}$			-	70	88	
Reverse Transfer Capacitance	$C_{RSS}$			-	33	37	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}$ , $I_D = 4.3\text{ A}$	-	8.9	12	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			-	1.5	1.7	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	2.1	2.6	
Gate Resistance	$R_g$	f = 1 MHz		1.1	-	6.66	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}$ , $R_L = 8.8\text{ }\Omega$ $I_D \cong 3.4\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\text{ }\Omega$		-	6	9	ns
Rise Time <sup>c</sup>	$t_r$			-	2.8	4.2	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			-	17	26	
Fall Time <sup>c</sup>	$t_f$			-	1.7	3	
<b>Source-Drain Diode Ratings and Characteristics <sup>b</sup></b>							
Pulsed Current <sup>a</sup>	$I_{SM}$			-	-	21.5	A
Forward Voltage	$V_{SD}$	$I_F = 2\text{ A}$ , $V_{GS} = 0\text{ V}$		-	0.75	1.1	V
Body diode reverse recovery time	$t_{rr}$	$I_F = 1.7\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$			16	32	ns
Body diode reverse recovery charge	$Q_{rr}$				13	26	nC
Reverse recovery fall time	$t_a$				13	-	ns
Reverse recovery rise time	$t_b$				3	-	
Body diode peak reverse recovery current	$I_{RM(REC)}$				-1.9	-	A

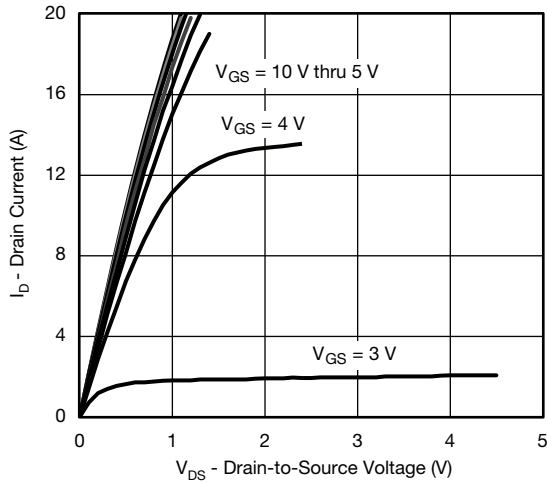
**Notes**

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

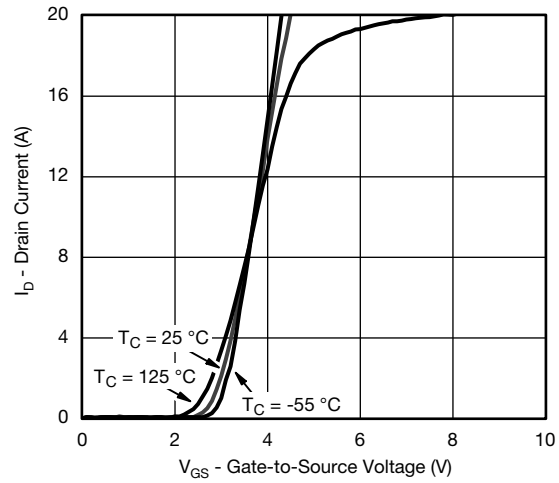
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



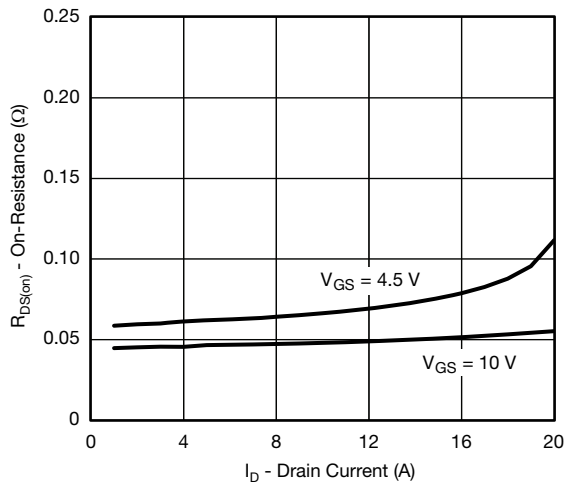
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



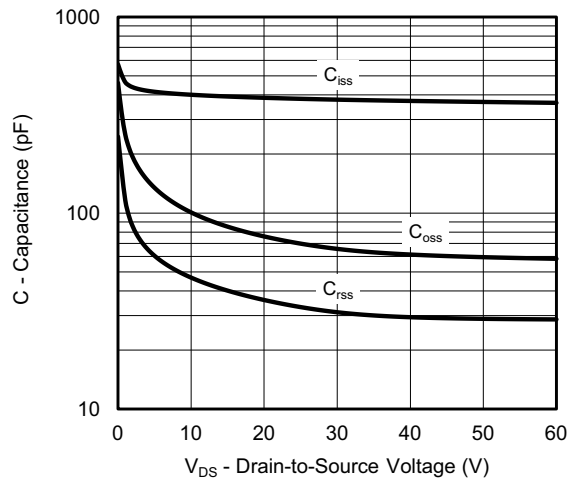
**Output Characteristics**



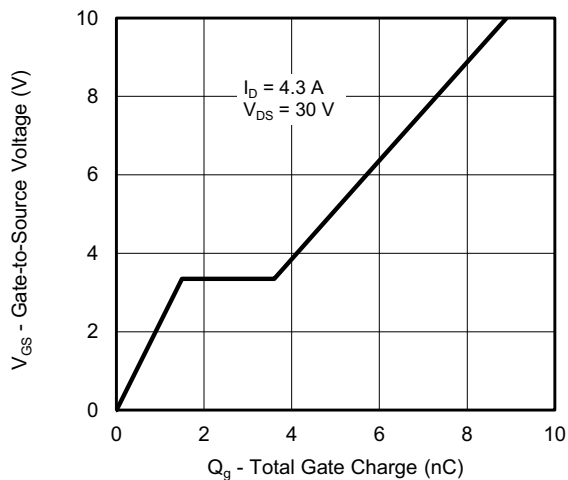
**Transfer Characteristics**



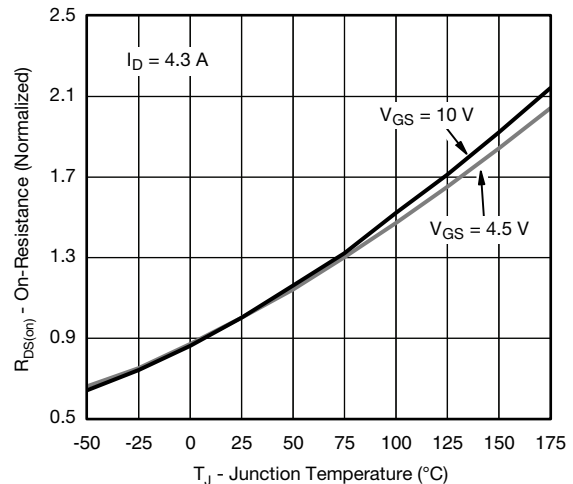
**On-Resistance vs. Drain Current**



**Capacitance**

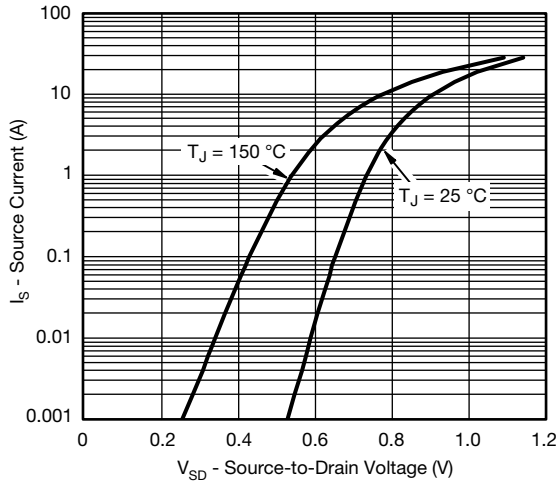


**Gate Charge**

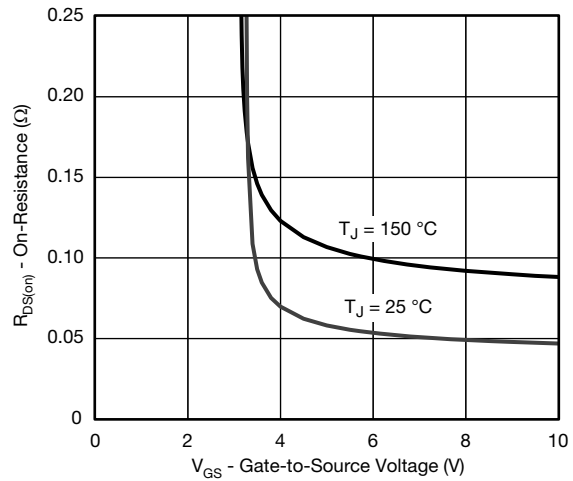


**On-Resistance vs. Junction Temperature**

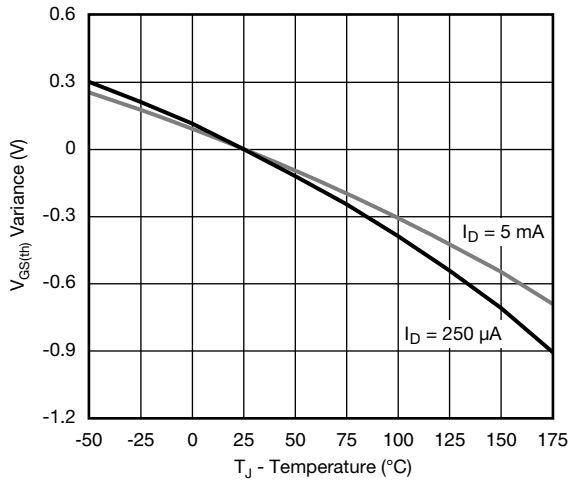
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



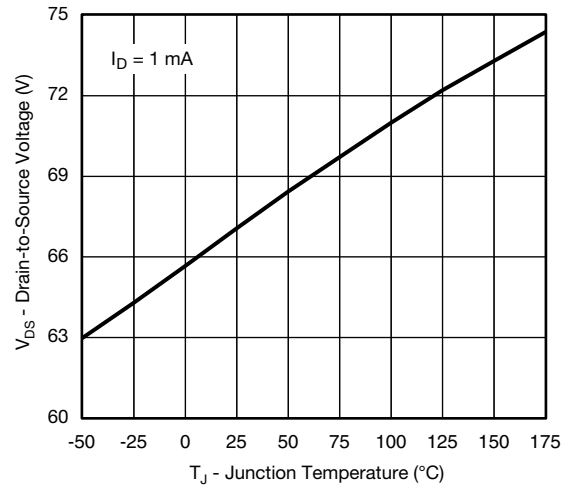
**Source Drain Diode Forward Voltage**



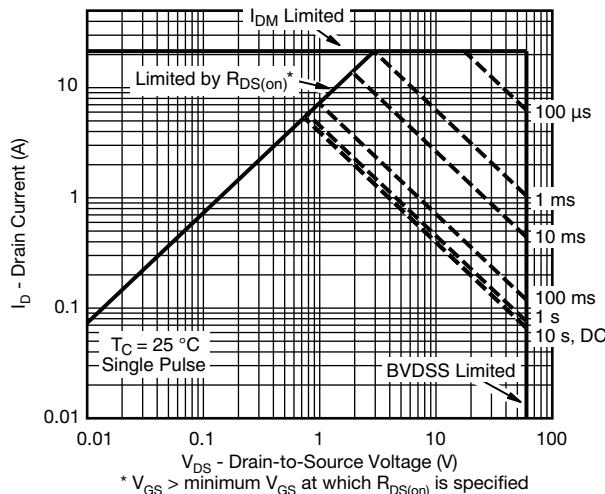
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



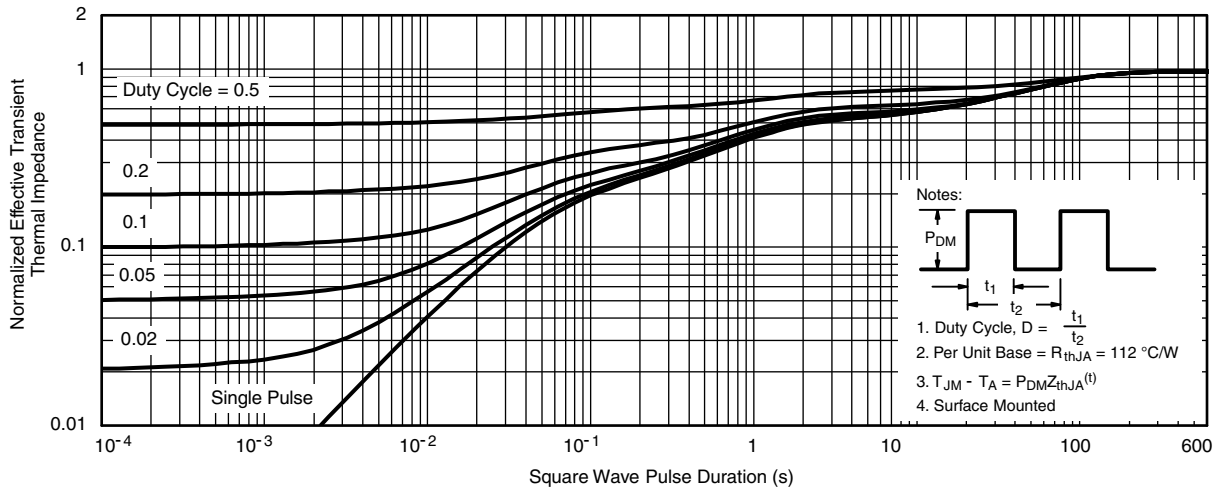
**Drain Source Breakdown vs. Junction Temperature**



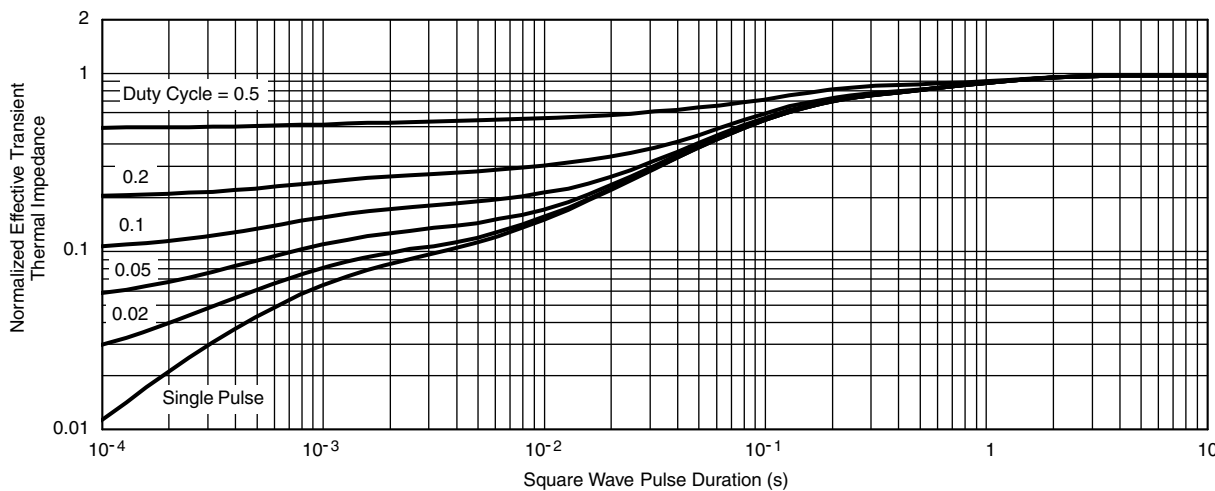
**Safe Operating Area**



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Case ( $25\text{ }^\circ\text{C}$ )
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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